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# P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
- 30	0.012 at V <sub>GS</sub> = - 10 V	- 11.4			
	0.019 at V <sub>GS</sub> = - 4.5 V	- 9.1			

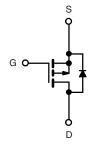
#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

- · Load Switches
  - Notebook PCs
  - Desktop PCs



P-Channel MOSFET

SO-8		
	Ω	D
	7	D
	6	D
	5	D
Top Viow		
	SO-8	8 7 6 5

Ordering Information: Si4425BDY-T1-E3 (Lead (Pb)-free)

Si4425BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	1A - 23 O, unite	1	1	1	
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	- 30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		V
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 11.4	- 8.8	^
	T <sub>A</sub> = 70 °C		- 9.1	- 7.0	
Pulsed Drain Current		I <sub>DM</sub>	- 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 2.1	- 1.3	
Mariana Barra Biratina	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.5	1.5	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.6	0.9	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana haratina ta Analianta	t ≤ 10 s	R <sub>thJA</sub>	40	50	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	15	18	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

## Vishay Siliconix



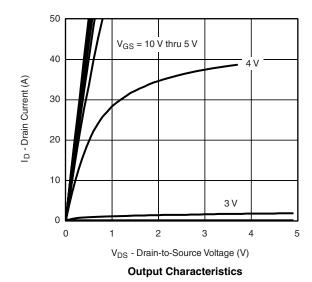
<b>SPECIFICATIONS</b> $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Oata Walkana Busin Oamani		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 50			Α	
Durin Course On Olate Desirters	B	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 11.4 A		0.010	0.012	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 9.1 A		0.015	0.019	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 11.4 A		29		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 2.5 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V	
Dynamic <sup>b</sup>	Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$			64	100		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -11.4 \text{ A}$		11		nC	
Gate-Drain Charge	Q <sub>gd</sub>			17		1	
Turn-On Delay Time	t <sub>d(on)</sub>			15	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		13	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$		100	150	ns	
Fall Time	t <sub>f</sub>			53	80		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = -2.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		41	80		

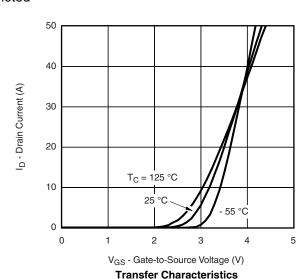
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

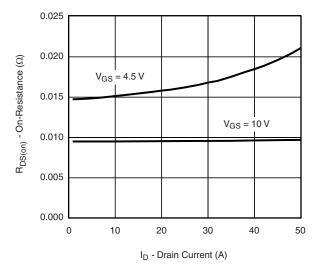




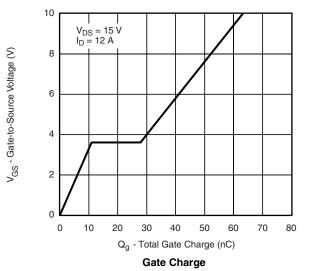




#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### **On-Resistance vs. Drain Current**



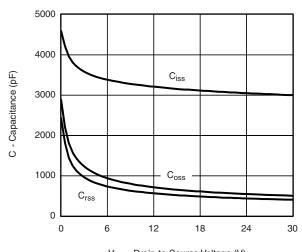
T<sub>J</sub> = 150 °C

T<sub>J</sub> = 25 °C

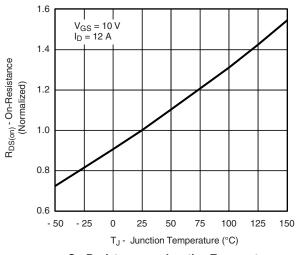
T<sub>J</sub> = 25 °C

V<sub>SD</sub> - Source-to-Drain Voltage (V)

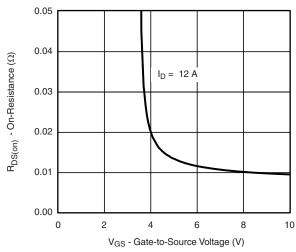
Source-Drain Diode Forward Voltage



V<sub>DS</sub> - Drain-to-Source Voltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

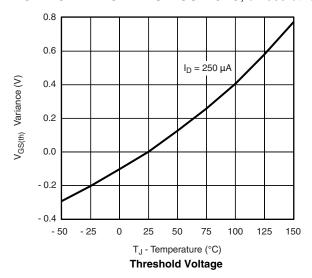
50

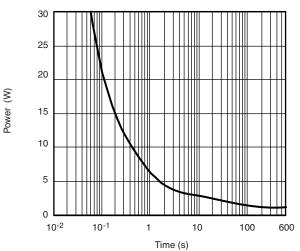
I<sub>S</sub> - Source Current (A)

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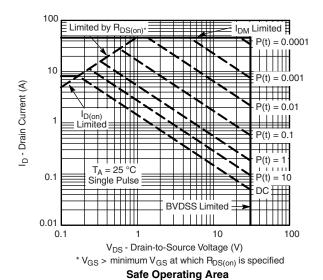
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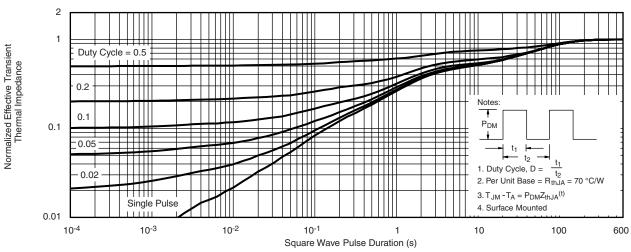
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

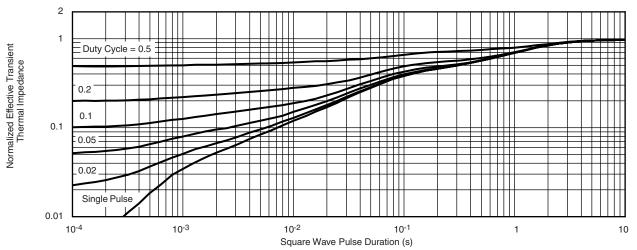




Normalized Thermal Transient Impedance, Junction-to-Ambient



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

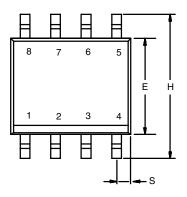


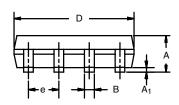
Normalized Thermal Transient Impedance, Junction-to-Foot

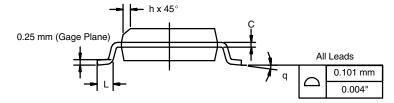
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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

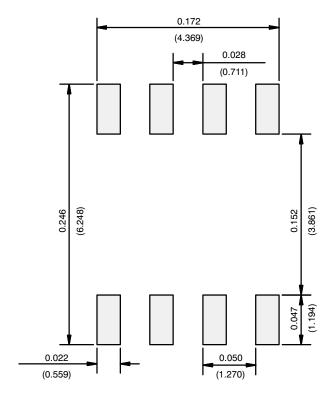
DWG: 5498

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# APPLICATION NOTE



#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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